

METHOD OF FORMING A MAGNETIC RANDOM ACCESS MEMORY STRUCTURE

Abstract of the Disclosure

A method for forming an MRAM bit is described that includes providing a covering layer over an integrated circuit structure. In one embodiment, the covering layer includes tantalum. A first mask layer is formed over the covering layer followed by a second mask layer. The first mask layer and second mask layer are etchable by the same etching process. The first and second mask layer are etched. Etch residue is removed from the first and second mask layers. The first mask layer is then selectively removed and the second mask layer remains.